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Correction: Exploring the feasibility and conduction mechanisms of P-type nitrogen-doped β-Ga_2O_3 with high hole mobility†

Congcong Ma,‡[ab] Zhengyuan Wu,‡[ab] Zhuoxun Jiang,[a] Ying Chen,[ab] Wei Ruan,[a] Hao Zhang,*[ac] Heyuan Zhu,[a] Guoqi Zhang,[a] Junyong Kang,[d] Tong-Yi Zhang,[e] Junhao Chu[b] and Zhilai Fang*[ab]

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The authors wish to point out that in the published article the footnote "‡ These authors contributed equally to this work." applies only to the authors Congcong Ma and Zhengyuan Wu.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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[a] *School of Information Science and Technology, and Academy for Engineering and Technology, Fudan University, Shanghai 200433, China. E-mail: zlfang@fudan.edu.cn*
[b] *Institute of Optoelectronics, Fudan University, Shanghai 200433, China*
[c] *Yiwu Research Institute of Fudan University, Chengbei Road, Yiwu City, Zhejiang 322000, China. E-mail: zhangh@fudan.edu.cn*
[d] *Collaborative Innovation Center for Optoelectronic Semiconductors and Efficient Devices, Department of Physics, Xiamen University, Xiamen 361005, China*
[e] *Materials Genome Institute, Shanghai University, 333 Nanchen Road, Shanghai 200444, China*

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‡ These authors contributed equally to this work.